

Fig. 2

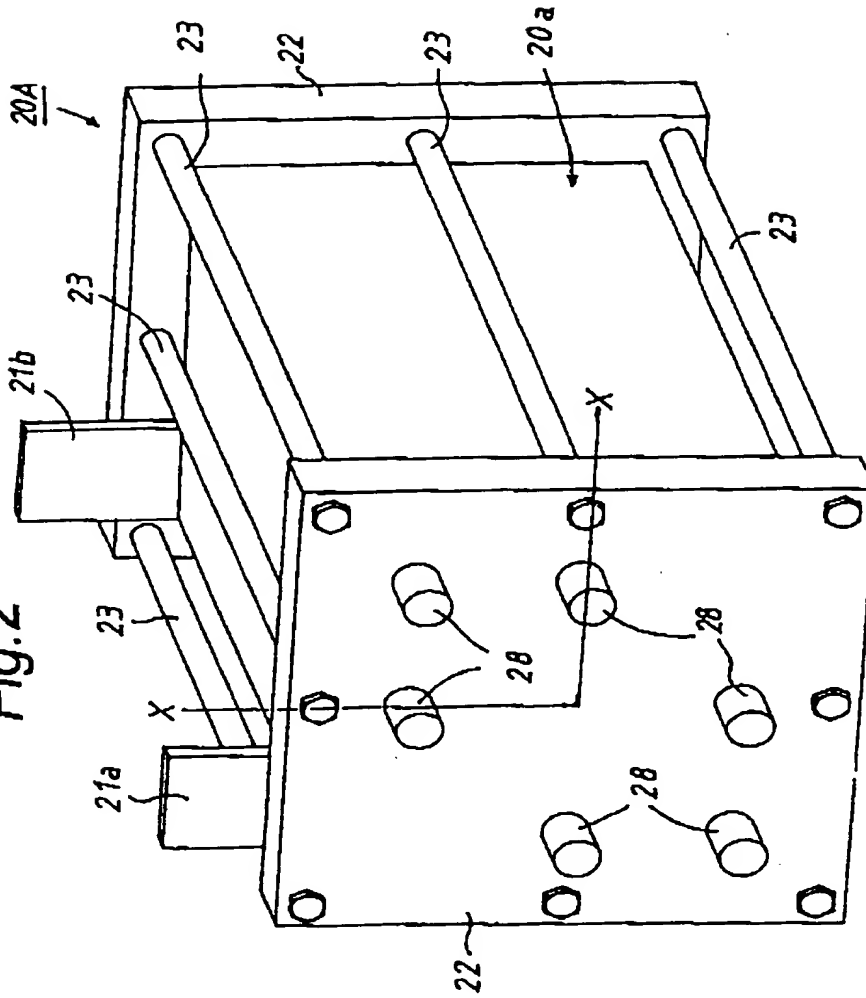


Fig.3

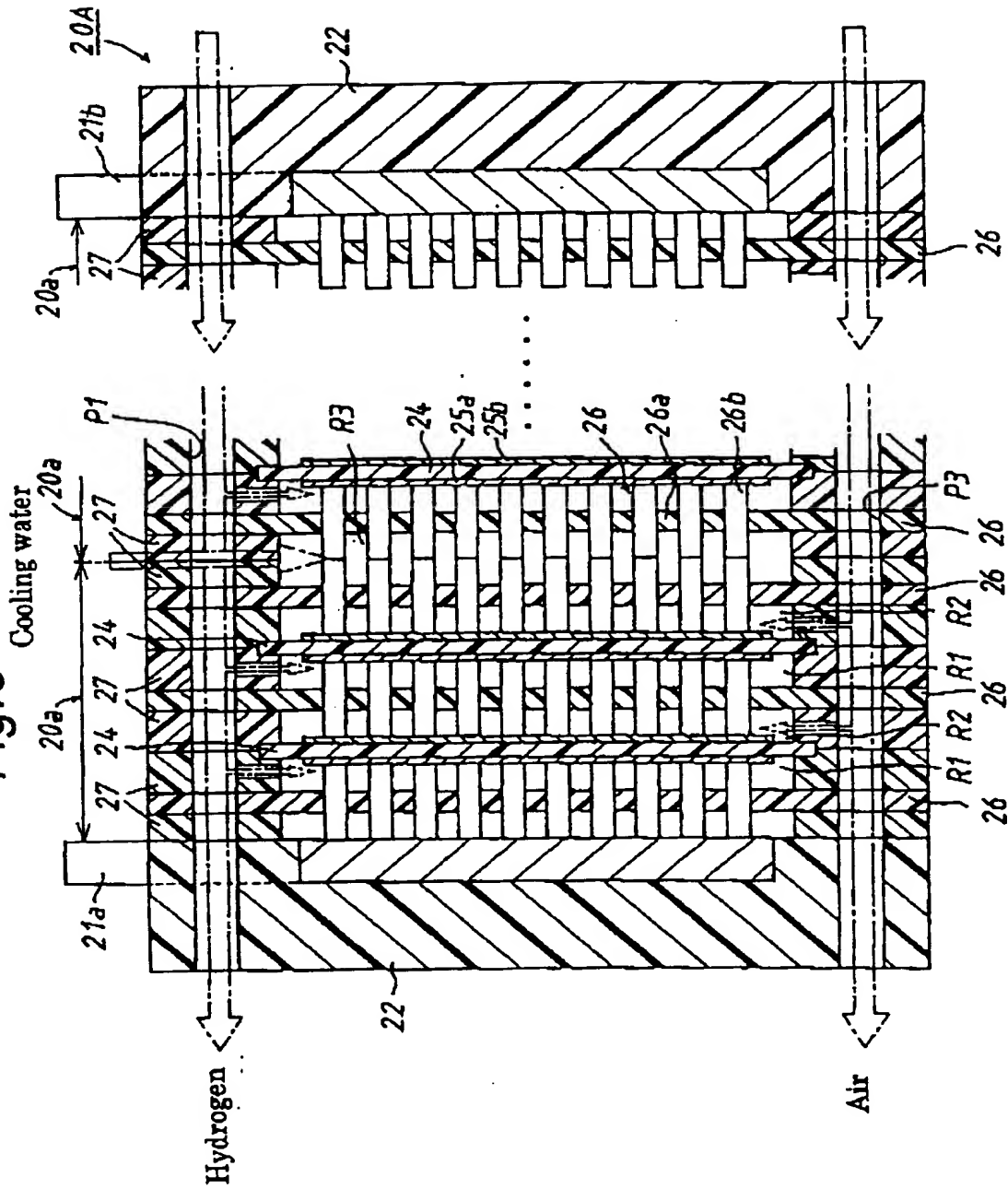
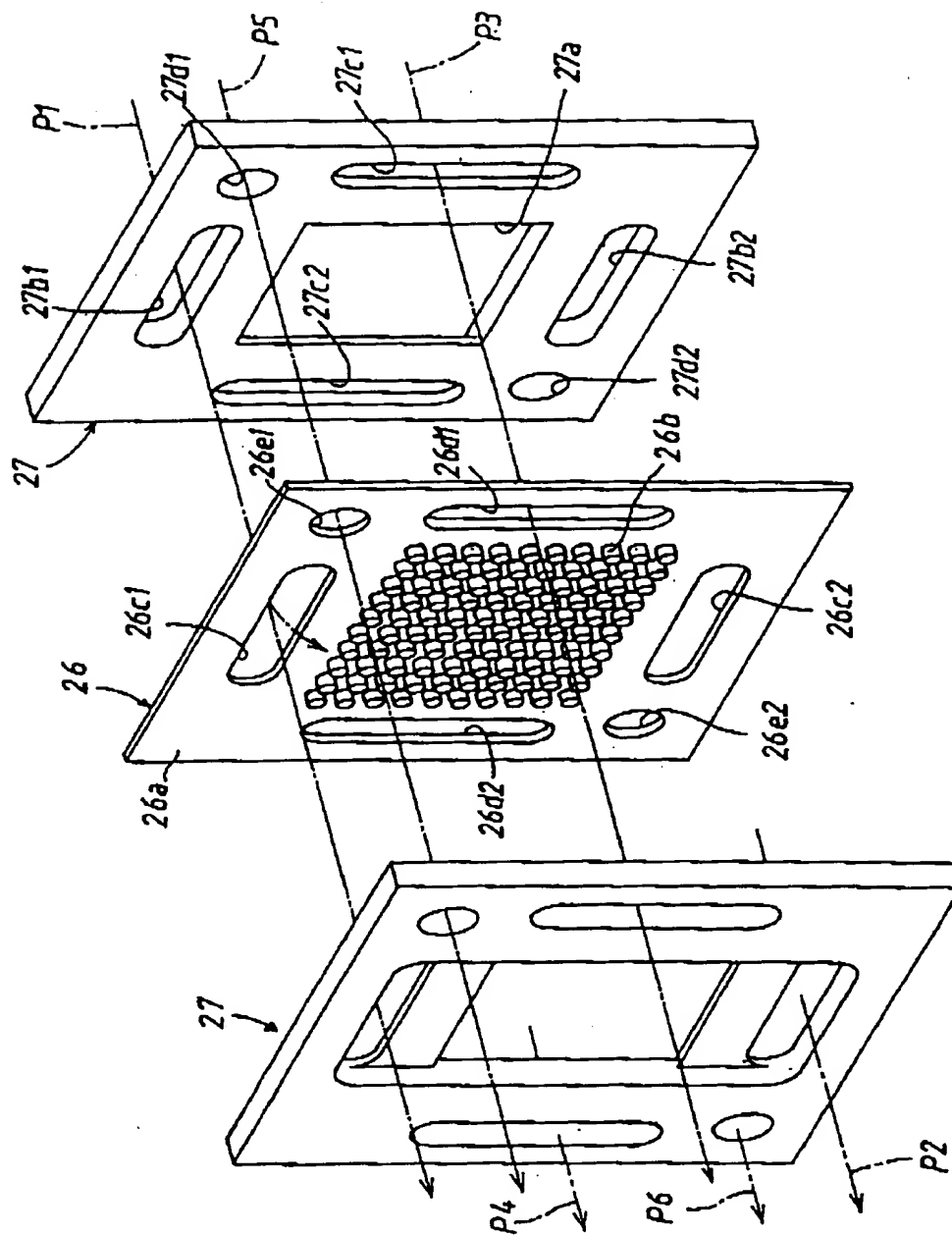


Fig. 4



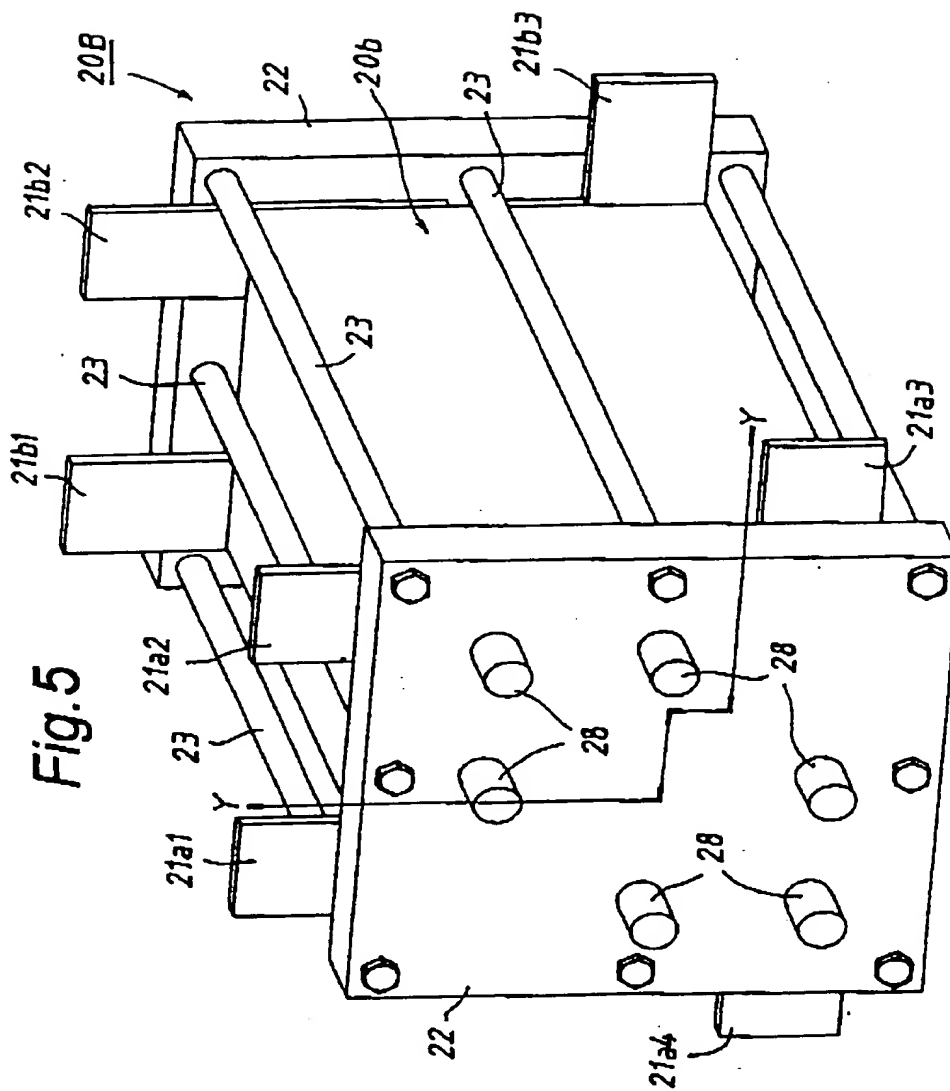


Fig. 6

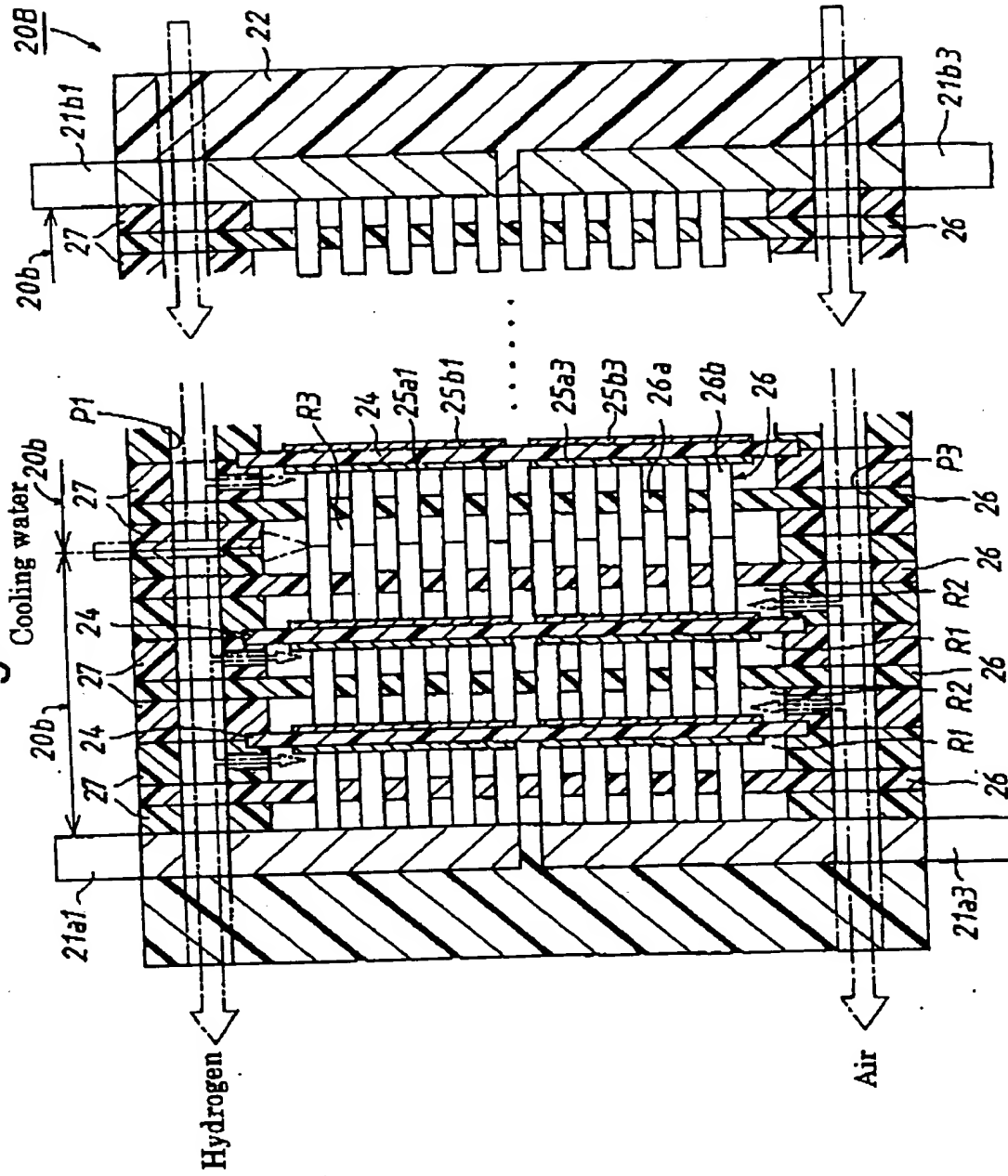
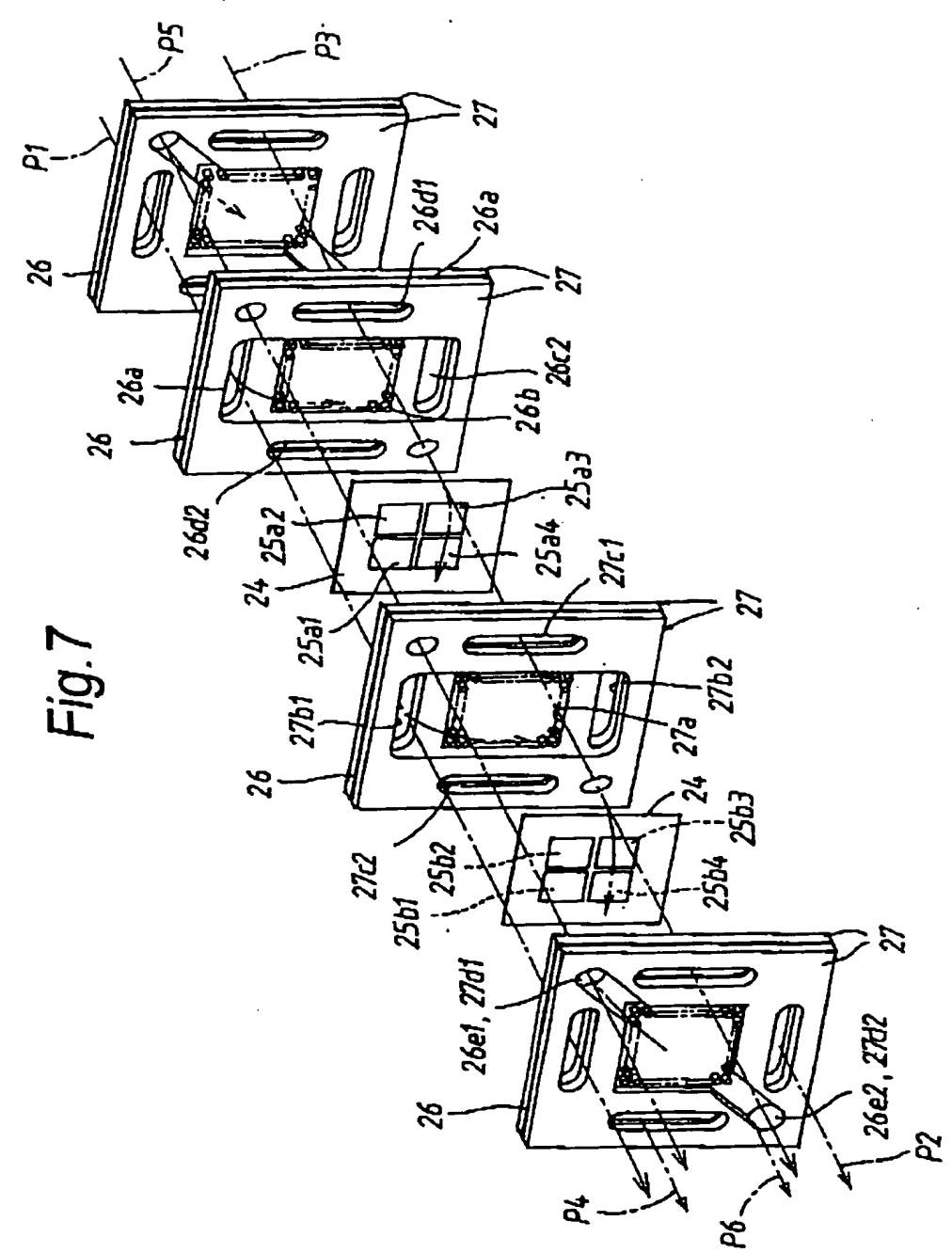


Fig. 7



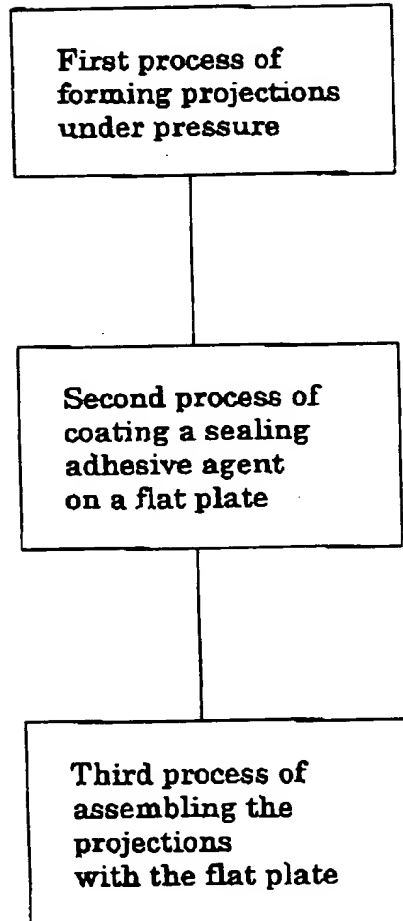
*Fig. 8*



Fig. 9

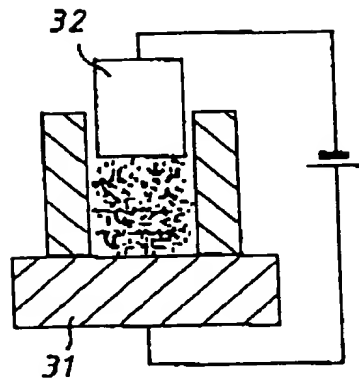


Fig. 10

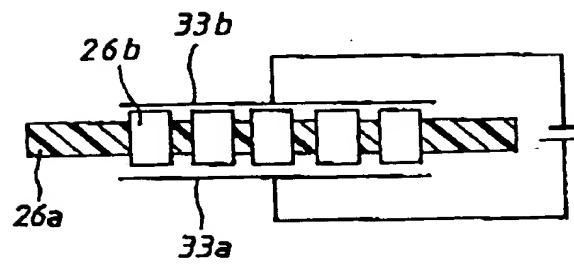


Fig. 1 is a cross-sectional view of a semiconductor device. The device consists of a substrate 34 with a top layer 34a and a bottom layer 34b. A central region 26a contains three rectangular blocks 26b. The blocks are connected to a common bus 34c. A separate component 35 is connected to the bus 34c via a wire 34d.

FIG. 1 is a cross-sectional view of a semiconductor device. The device consists of a substrate 35. A central channel 26a is formed in the substrate. On either side of the channel are regions 26b and 26c. A gate structure 35a is formed on top of the substrate. A contact region 35b is formed on the left side of the substrate. A cross-section line 26a1 is indicated.